



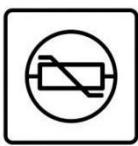
ESD



TVS



TSS



MOV



GDT



PLED

## **CSD25402Q3A-MS**

### **Product specification**

## Description

The CSD25402Q3A-MS uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

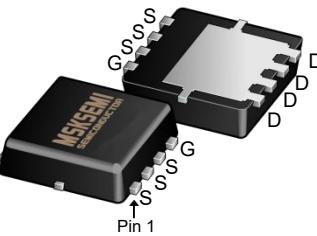
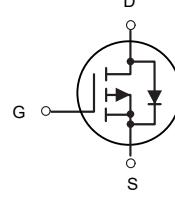
## Features

- $V_{DS} = -20V$   $I_D = -60A$
- $R_{DS(ON)} < 10m\Omega$  @  $V_{GS} = -4.5V$

## Application

- Battery protection
- Load switch
- Uninterruptible power supply

## Reference News

DFN3X3-8L	P-Channel MOSFET	Marking
		

## Absolute Maximum Ratings ( $T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 12$	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	-60	A
$I_D @ T_c = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	-30	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-78	A
$P_D @ T_c = 25^\circ C$	Total Power Dissipation <sup>4</sup>	22	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance Junction-ambient <sup>1</sup>	75	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	4.2	°C/W

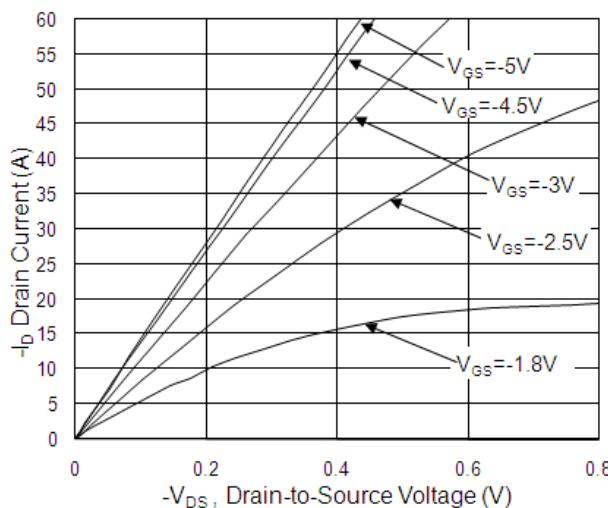
**Electrical Characteristics** (T<sub>J</sub>=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-20	---	---	V
△BV <sub>DSS</sub> /△T <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =-1mA	---	-0.012	---	V/°C
R <sub>DSS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-10A	---	7	10	mΩ
		V <sub>GS</sub> =-2.5V , I <sub>D</sub> =-8A	---	9	12	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-0.4	-0.7	-1.0	V
△V <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	2.94	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	---	---	1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±12 V , V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-5V , I <sub>D</sub> =-10A	---	43	---	S
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-10V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-10A	---	35	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	5.0	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	10	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-10V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-10A	---	12.0	---	ns
T <sub>r</sub>	Rise Time		---	40.0	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	30	---	
T <sub>f</sub>	Fall Time		---	10	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , f=1MHz	---	2800	---	pF
C <sub>oss</sub>	Output Capacitance		---	690	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	590	---	
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	-60.0	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,4</sup>		---	---	---	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25°C	---	---	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =-10A , dI/dt=100A/μs , T <sub>J</sub> =25°C	---	27	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	17.8	---	nC

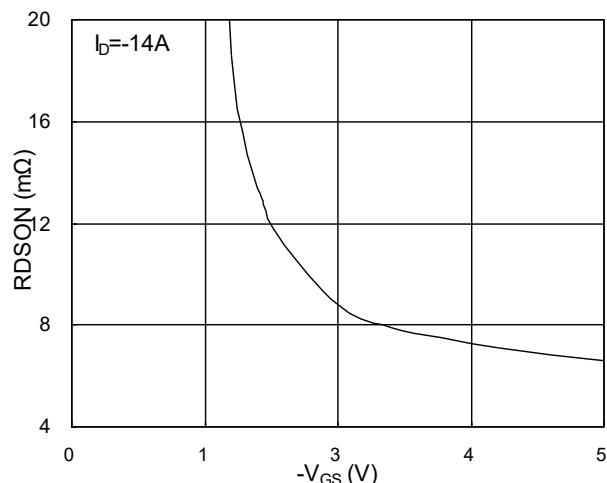
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The power dissipation is limited by 150°C junction temperature
- 4.The data is theoretically the same as I<sub>band</sub> I<sub>DM</sub>, in real applications , should be limited by total power dissipation.

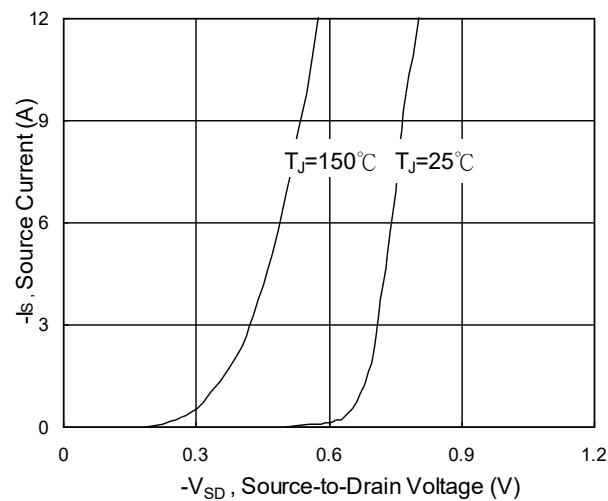
## Typical Characteristics



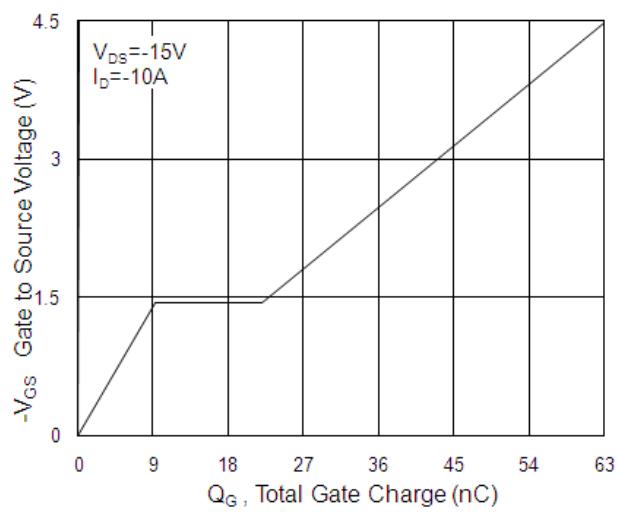
**Fig.1 Typical Output Characteristics**



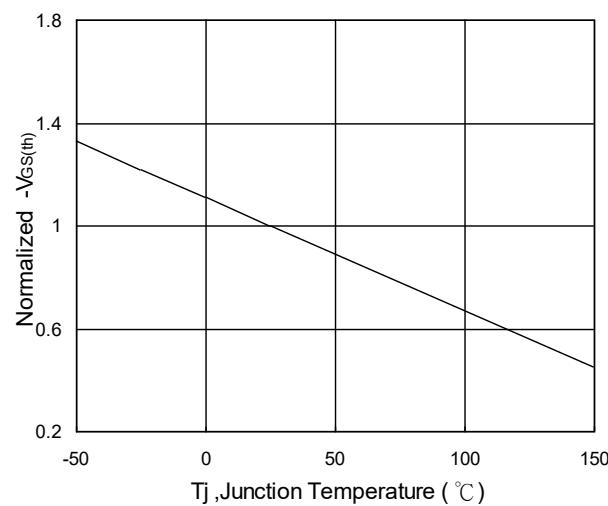
**Fig.2 On-Resistance vs. G-S Voltage**



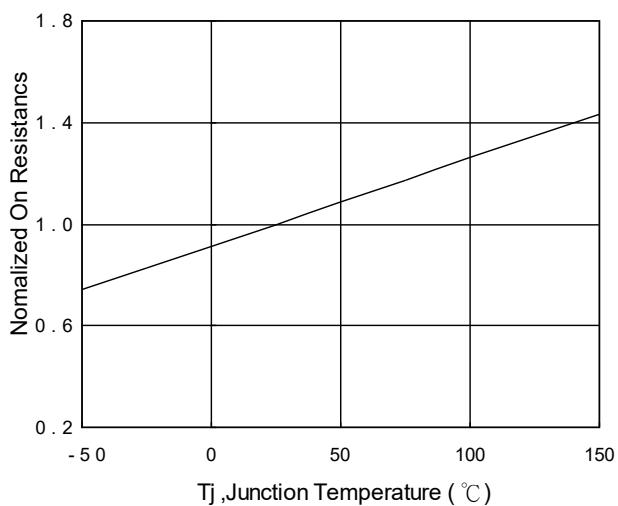
**Fig.3 Forward Characteristics of Reverse**



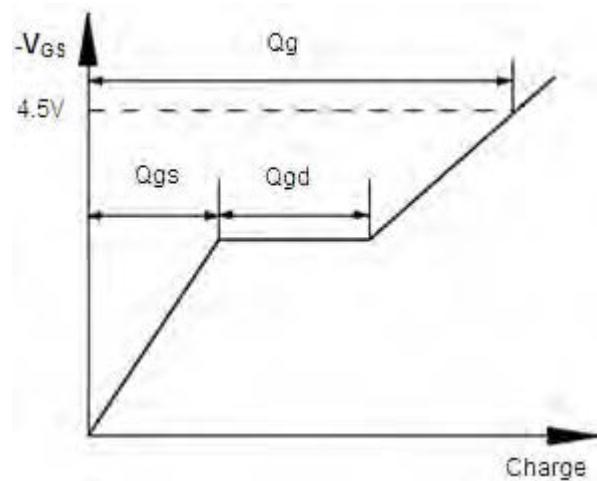
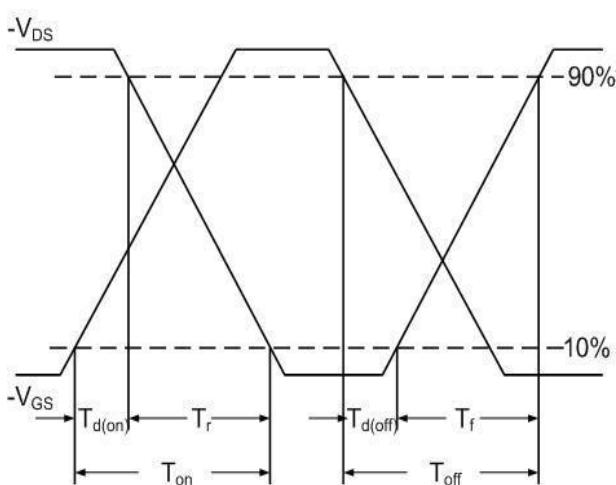
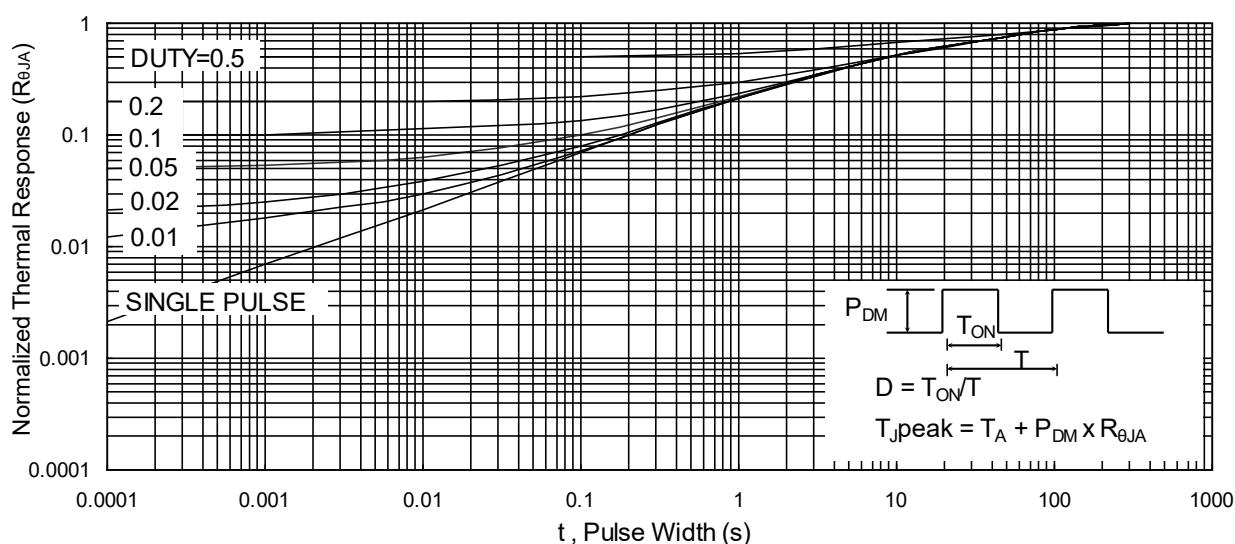
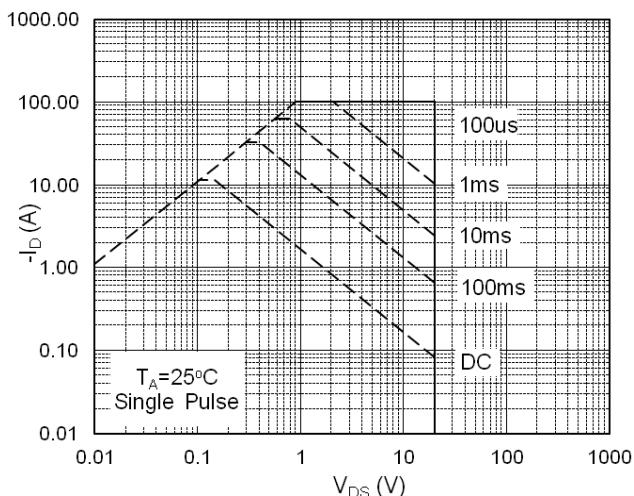
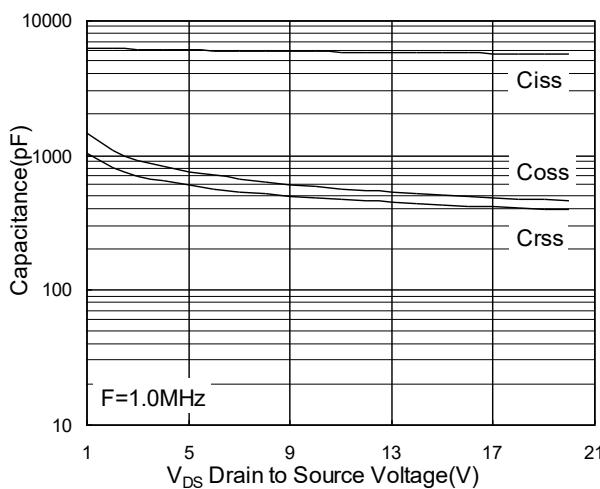
**Fig.4 Gate-charge Characteristics**

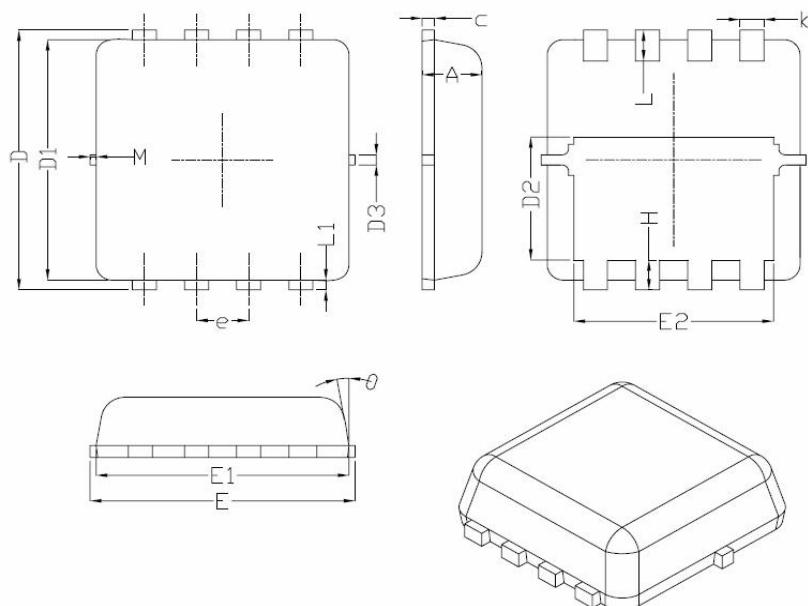


**Fig.5 Normalized  $V_{GS(th)}$  vs.  $T_J$**



**Fig.6 Normalized  $R_{DSON}$  vs.  $T_J$**



**DFN3X3-8L Package Information**


Symbol	Dimensions In Millimeters		
	Min.	Nom.	Max.
A	0.70	0.75	0.80
b	0.25	0.30	0.35
c	0.10	0.15	0.25
D	3.25	3.35	3.45
D1	3.00	3.10	3.20
D2	1.48	1.58	1.68
D3	-	0.13	-
E	3.20	3.30	3.40
E1	3.00	3.15	3.20
E2	2.39	2.49	2.59
e	0.65BSC		
H	0.30	0.39	0.50
L	0.30	0.40	0.50
L1	-	0.13	-
M	*	*	0.15
θ	10 °		
	12 °		

**REEL SPECIFICATION**

P/N	PKG	QTY
CSD25402Q3A-MS	DFN3X3-8L	5000

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